Q.P. Code: 16EC410

SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR (AUTONOMOUS)

B.Tech II Year II Semester Regular & Supplementary Examinations May 2019

B.Tech II Year II Semester Regular & Supplementary Examinations May 2019 PULSE AND DIGITAL CIRCUITS				
(Electronics and Communication Engineering)				
Time: 3 hours Max. Marks: 60			60	
UNIT-I				
1	a	Show that a high pass circuit with a small time constant acts as differentiator.	6M	
	b	A 10v step is switched on to a $50k\Omega$ resistor in series with a $500pf$ capacitor.calculate the rise time of the capacitor voltage, the time for the capacitor to charge 63.2% of its maximum voltage, and the time for the capacitor to be completely charged	6M	
	OR			
2	a	With the help of a neat circuit diagram, explain the working of a two-level diode clipper.	6M	
	b	Define clamper. With the help of neat circuit diagrams and output waveforms, explain the working of positive peak and negative peak clamping circuits UNIT-II	6M	
3	a	Ellaborte about piece-wise linear approximation for a semiconductor diode Characteristics.	6M	
	b	Design the transistor as a switch and draw the output characteristics OR	6M	
•	4	Explain the operation of collector coupled astable multivibrator and draw its output waveforms UNIT-III	12M	
	5	Explain the working of diode as a switch and draw the output characteristics. OR	12M	
6	a	Explain the basic principles of Miller and Bootstrap time-base generators.	6M	
	b	Compare miller and bootstrap time base generators	6M	
		UNIT-IV		
7	a	Compare unidirectional and bidirectional sampling gates	6M	
	b	Why the sampling gates are called linear gates?	6M	
8	a	OR With the help of neat diagram explain the working of a four diode sampling gate.	6M	
O	b	Derive expressions for its gain (A) and Vmin of a four diode sampling gate. UNIT-V	6M	
	a	Explain the synchronization of sweep circuit with symmetric signals.	6M	
9	b	How a sine wave frequency division is done with a sweep circuit? OR	6M	
1	.0	With the help of neat circuit diagram and truth table explain the working of (i) DTL NAND gate (ii) RTL NAND gate. *** END ***	12M	